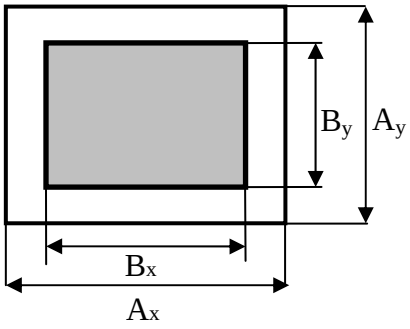
VSP-MIKRON

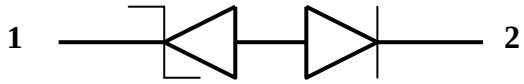
RoHS

Rev.2. Jan. 2011.

SM-3,3V2

Chip TVS diode for TVS array TClamp3302.





Schematic and pinning diagram.

Mechanical date: A_x=1450um, A_y=580um.
B_x=1270um, B_y=400um
Chip thickness: 138+/-12um
Scribe Line width - 60um.
Top Metal: Al - for wire bonding, d=4.0+/-0.2 um.
Back side: Ti-Ni-Ag for soldering.
Top Side - pin 1 – Cathode, **Back Side** - pin 2.–Anode

Limiting values

Parameter	Symbol	Conditions	Value	Unit
Working Peak Reverse Voltage	V_{RWM}		3,3	V
Peak Pulse Power	P_{pp}	t_p= 2/10uS	2500*	W
Max. Peak Pulse Current	Ipp	t_p= 2/10uS	120*	A
Max. Peak Pulse Current	I_{PP}	t_p= 8/20uS	95,0*	A
Electrostatic discharge	V_{ESD}	IEC 61000-4-2. Level-4.	+/-30,0 –Contact. +/-30,0 – Air.	kV
Max.Junction Temperature	T_j	-	+125	ºC

Characteristics (Tj=25ºC)

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_R	Diode reverse leakage current.	V_R=3,3V; T=25 ºC. "+" on pin 1.	-	-	0,9	uA
V_{PT}	Punch-Through Voltage.	I_{PT}=2uA; T=25 ºC.	3,5	-	-	V
V_{SB}	Snap-Back Voltage	I_{SB}=50mA	2,8	-	-	V
C_j	Diode capacitance .	F=1MHz, V_{dc}=0 V.	-	250	-	pF
V_{CL}	Clamping voltage	I_R=100A, t_p=2/10uS	-	-	19,0*	V

*- For Device testing.